TECHNICAL DATA DATA SHEET 175, REV. B

HERMETIC AXIAL LEAD/MELF RECTIFIER

DESCRIPTION: A 600 VOLT, 1.0 AMP, 250 NANOSECOND AXIAL LEAD MELF RECTIFIER

MAXIMUM RATINGS

All ratings are at $T_A = 25^{\circ}$ C unless otherwise specified.

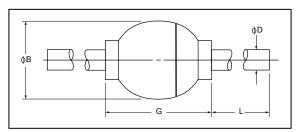
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RATING	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Peak Inverse Voltage (PIV)	-	-	-	600	Vdc
Average DC Output Current (I _o)	T _A = +75 °C	-	-	1.0	Amps
Average DC Output Current (I _o)	T _A = +100 °C	-	-	.75	Amps
Peak Single Cycle Surge Current (I _{fsm})	t _p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	25	Amps(pk)
Operating and Storage Temp. (T _{op} & T _{stq})	-	-65	-	+175	°C
Thermal Resistance (θ _{JL})	d = 0.375"	_	_	38	° C/W
Thermal Resistance (θ _{JEC})	Junction to end caps	-	-	7.0	° C/W

ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Maximum Forward Voltage (V _f)	I _f = 3.0A (300 μsec pulse, duty cycle < 2%)	-	-	1.6	Volts
Maximum Instantaneous	T _A = 25° C	-	-	0.5	μAmps
Reverse Current At Rated PIV (I _R)	T _A = 100° C			25	
Reverse Recovery Time	$I_f = 0.5A, I_r = 0.5A,$	-	-	250	nsec
(t _{rr})	I _{rr} = 50mA				

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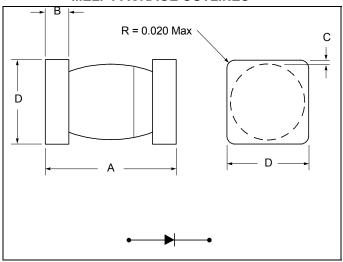
AXIAL LEAD RECTIFIER OUTLINES



Note: Cathode side of device is indicated by a dark band marked on body.

PACKAGE	DIMENSIONS - INCHES / MILLIMETERS				
STYLE	φВ	φD	G	L	
102	.065/.110	.026/.033	.130/.225	1.00/1.30	
	1.65/2.79	.66/.84	3.30/5.72	25.4/33.0	

MELF PACKAGE OUTLINES



Note: Cathode side of device is indicated by a dark band marked on body.

PACKAGE	DIMENSIONS - INCHES / MILLIMETERS				
STYLE	Α	В	С	D	
MELF-1	.168/.230	0.019/.028	.003 Min	.091/.128	
	4.2/5.9	.48/.72	.076 Min	3.4/3.8	

SENSITRON

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